Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	30	mA
				40	
I_H	I_T =100mA		MAX.	25	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	5	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				30	

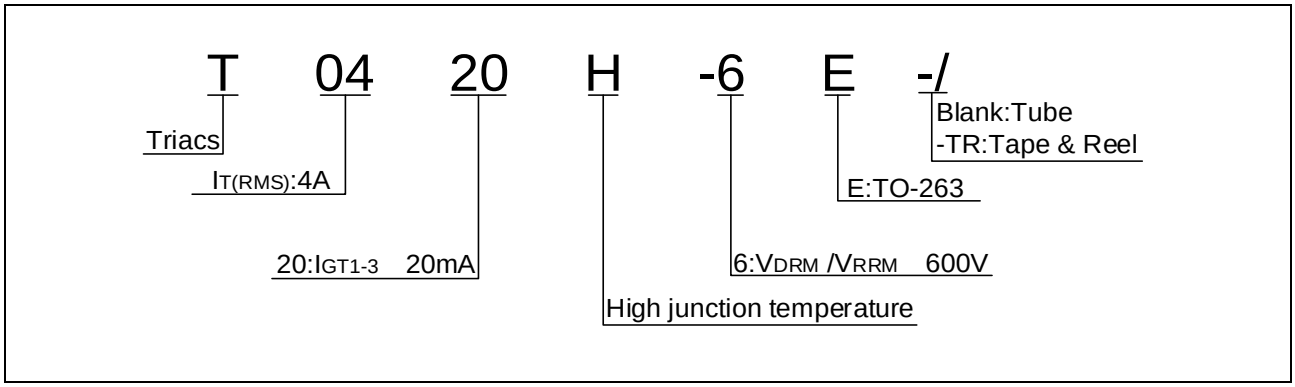
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =5.5A t_p=380μs	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=150	0.6	V
R_D	Dynamic resistance	T_j=150	129	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	0.8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	/W
$R_{th(j-a)}$	junction to ambient (AC, in free air, S=2cm^2)	55	/W

ORDERING INFORMATION



MARKING

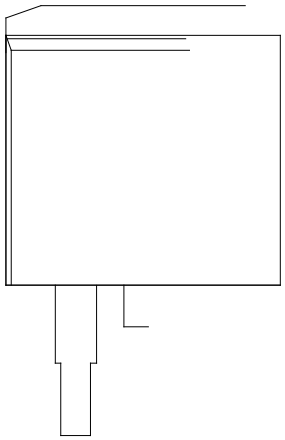
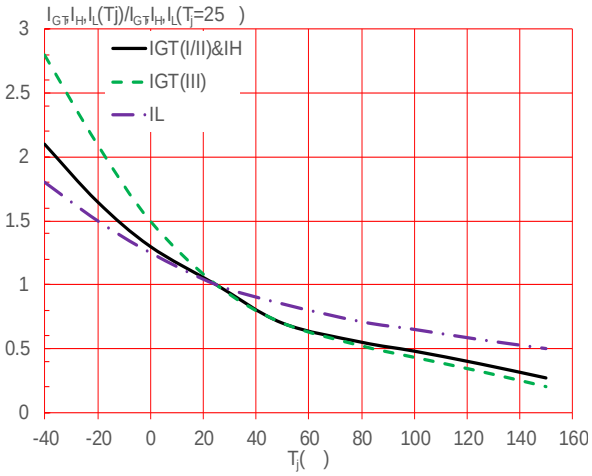
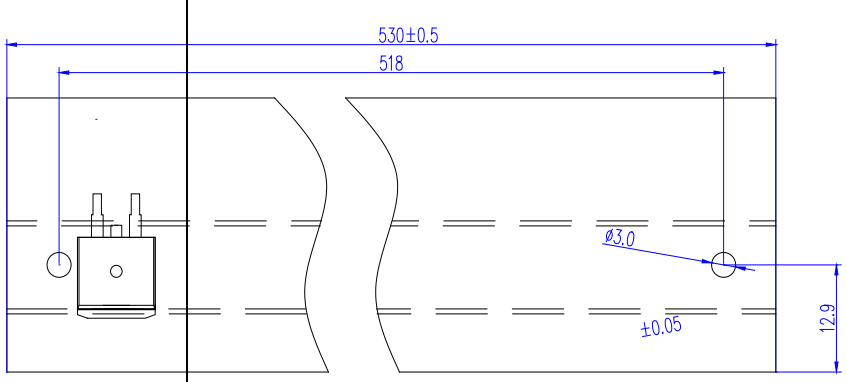
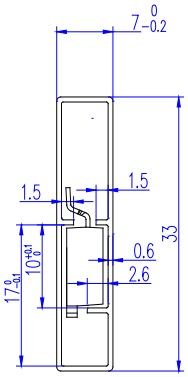


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



DELIVERY MODE





PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON

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